



74VHC03

QUAD 2-INPUT OPEN DRAIN NAND GATE

- HIGH SPEED: $t_{PD} = 3.7ns$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu A$ (MAX.) at $T_A = 25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $5.5V$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 03
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: $V_{OLP} = 0.8V$ (MAX.)

DESCRIPTION

The 74VHC03 is an advanced high-speed CMOS QUAD 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provides high noise immunity and stable output.

This device can, with an external pull-up resistor, be used in wired AND configuration. This device can also be used as a led driver and in any other application requiring a current sink.

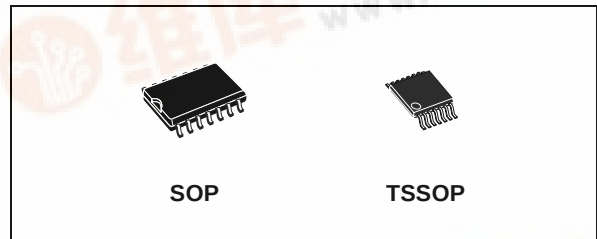


Table 1: Order Codes

PACKAGE	T & R
SOP	74VHC03MTR
TSSOP	74VHC03TTR

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

Figure 1: Pin Connection And IEC Logic Symbols

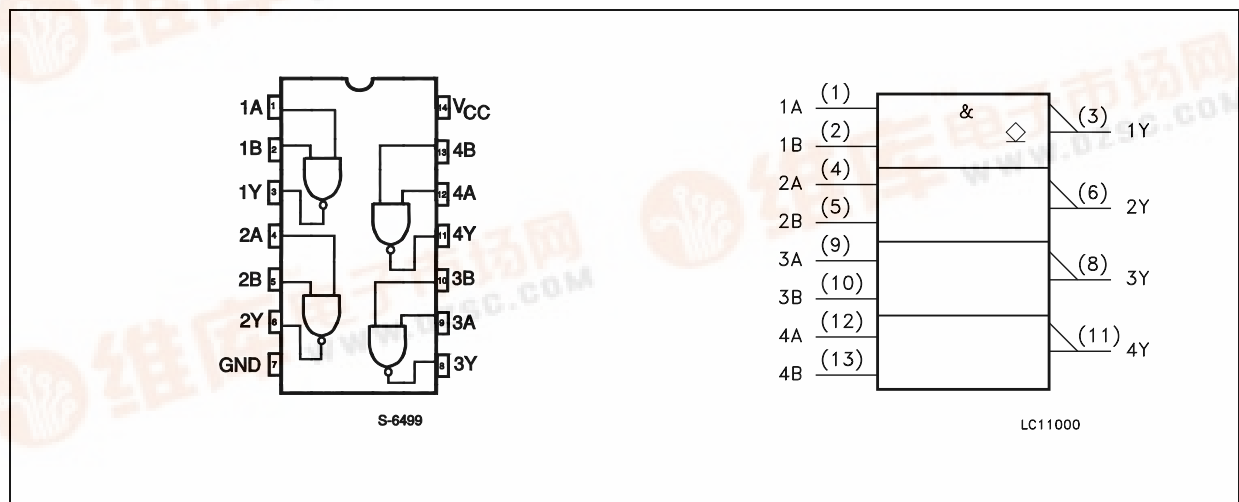


Figure 2: Input Equivalent Circuit

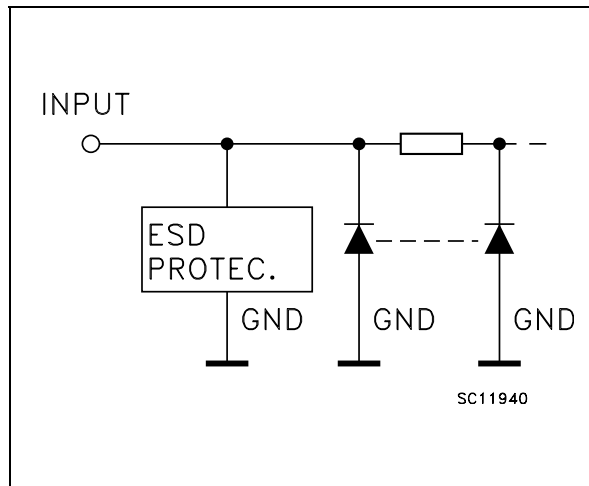


Table 2: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

Table 3: Truth Table

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z: High Impedance

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Table 5: Recommended Operating Conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V _{CC} = 3.3 ± 0.3V) (V _{CC} = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V

1) V_{IN} from 30% to 70% of V_{CC}

Table 6: DC Specifications

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		3.0 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	
V _{OL}	Low Level Output Voltage	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _{OZ}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.25		± 2.5		± 2.5	μA
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			2		20		20	μA

Table 7: AC Electrical Characteristics (Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition			Value						Unit	
		V _{CC} (V)	C _L (pF)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PZL}	Output Enable Time	3.3 ^(*)	15	R _L = 1 KΩ		5.5	7.9	1.0	9.5	1.0	9.5	ns
		3.3 ^(*)	50	R _L = 1 KΩ		8.0	11.4	1.0	13.0	1.0	13.0	
		5.0 ^(**)	15	R _L = 1 KΩ		3.7	5.5	1.0	6.5	1.0	6.5	
		5.0 ^(**)	50	R _L = 1 KΩ		5.2	7.5	1.0	8.5	1.0	8.5	
t _{PLZ}	Output Disable Time	3.3 ^(*)	50	R _L = 1 KΩ		8.0	11.4	1.0	13.0	1.0	13.0	ns
		5.0 ^(**)	50	R _L = 1 KΩ		5.2	7.5	1.0	8.5	1.0	8.5	

(*) Voltage range is 3.3V ± 0.3V

(**) Voltage range is 5.0V ± 0.5V

Table 8: Capacitive Characteristics

Symbol	Parameter	Test Condition	Value								Unit
			T _A = 25°C			-40 to 85°C		-55 to 125°C			
			Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
C _{IN}	Input Capacitance			4	10		10		10	pF	
C _{OUT}	Output Capacitance			5						pF	
C _{PD}	Power Dissipation Capacitance (note 1)			6						pF	

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per gate)

Table 9: Dynamic Switching Characteristics

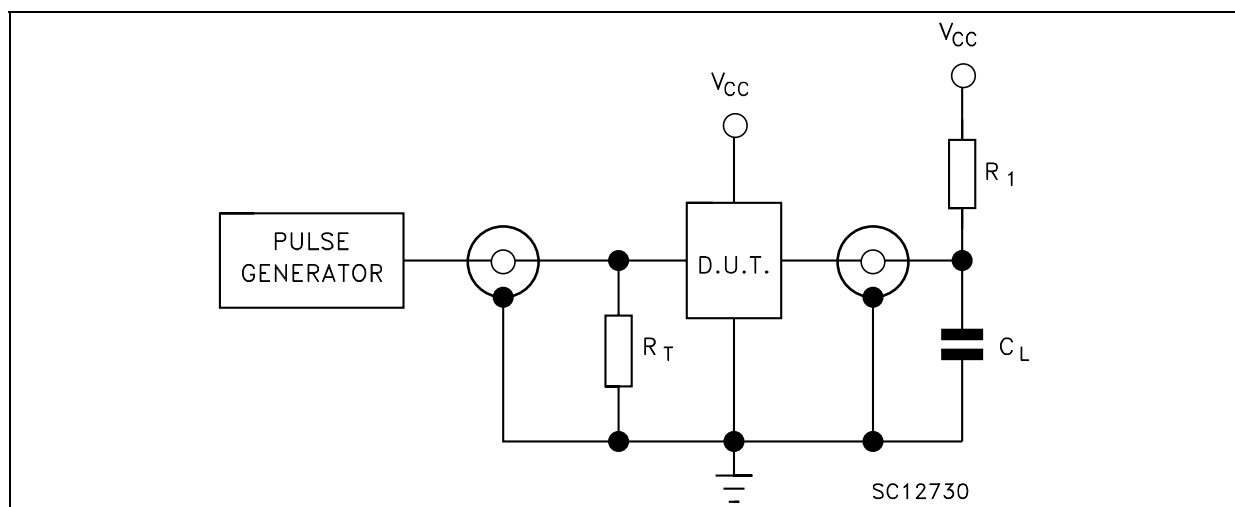
Symbol	Parameter	Test Condition		Value								Unit
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C			
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	5.0	C _L = 50 pF		0.3	0.8					V	
V _{OLV}				-0.8	-0.3							
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0		3.5							V	
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0					1.5					V

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 5.0V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 5.0V. Inputs under test switching: 5.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), $f=1\text{MHz}$.

Figure 3: Test Circuit

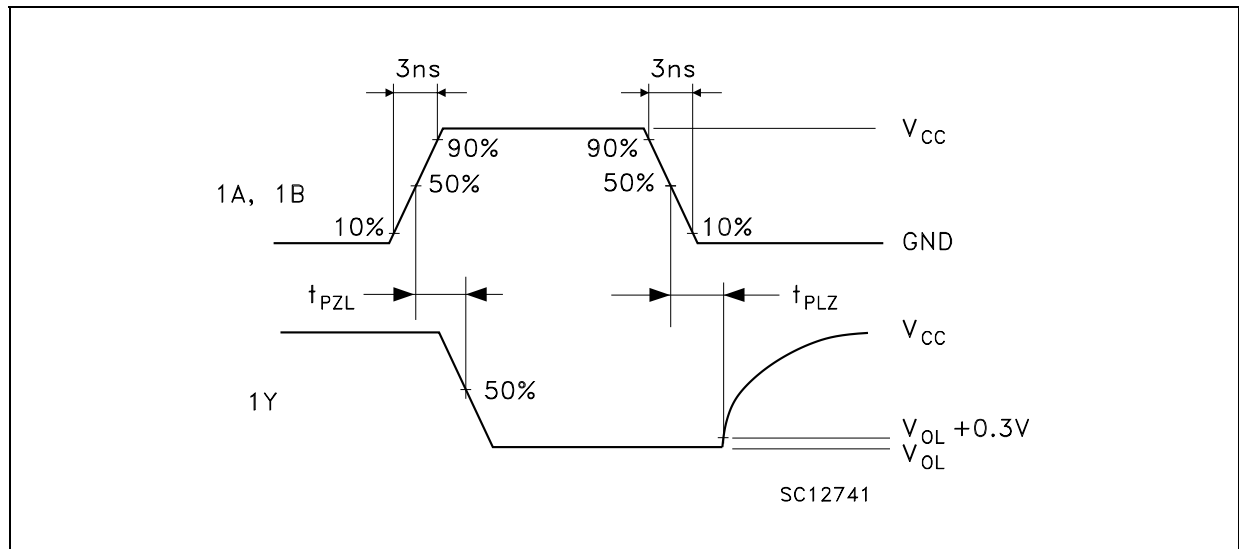


$C_L = 15/50\text{pF}$ or equivalent (includes jig and probe capacitance)

$R_L = R_1 = 1\text{K}\Omega$ or equivalent

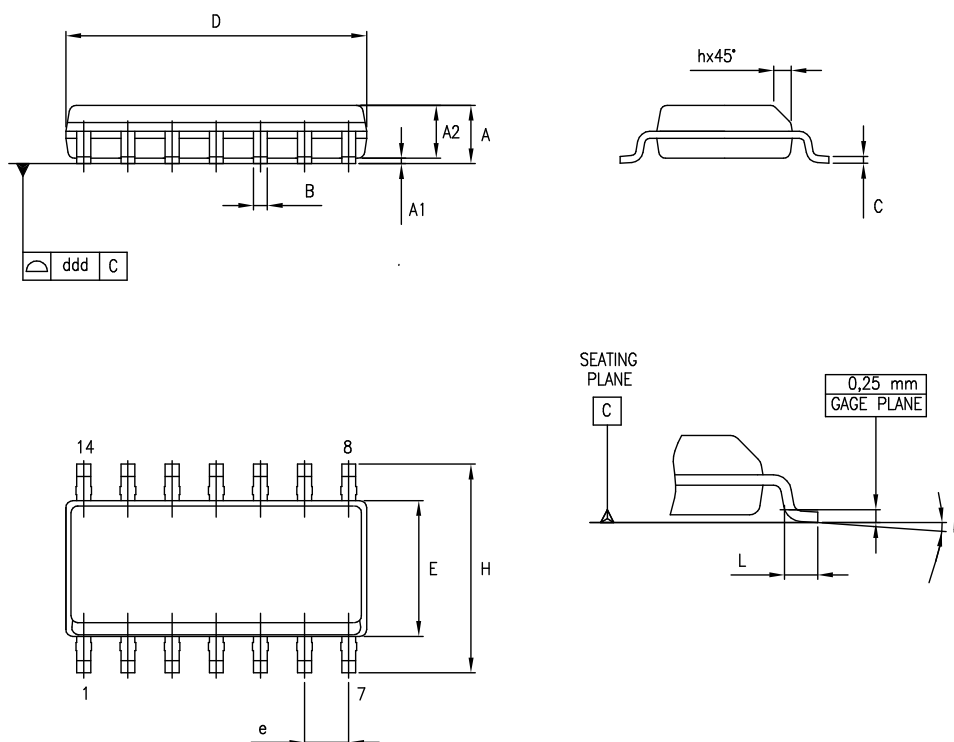
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 4: Waveform - Propagation Delays (f=1MHz; 50% duty cycle)



SO-14 MECHANICAL DATA

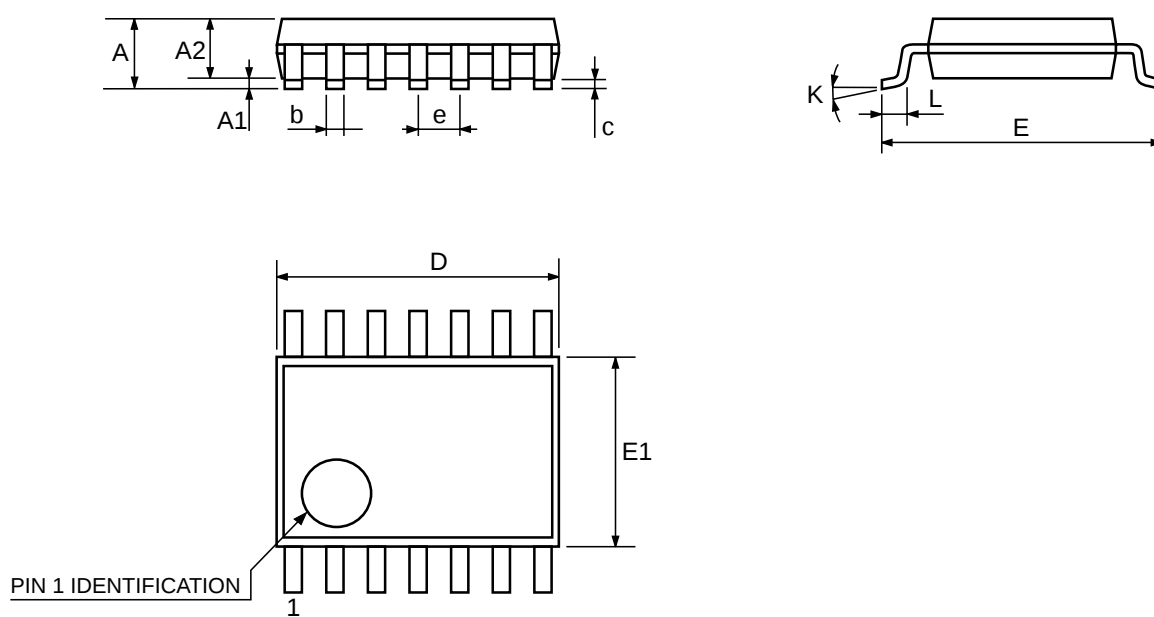
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	1.35		1.75	0.053		0.069
A1	0.1		0.25	0.004		0.010
A2	1.10		1.65	0.043		0.065
B	0.33		0.51	0.013		0.020
C	0.19		0.25	0.007		0.010
D	8.55		8.75	0.337		0.344
E	3.8		4.0	0.150		0.157
e		1.27			0.050	
H	5.8		6.2	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.4		1.27	0.016		0.050
k	0°		8°	0°		8°
ddd			0.100			0.004



0016019D

TSSOP14 MECHANICAL DATA

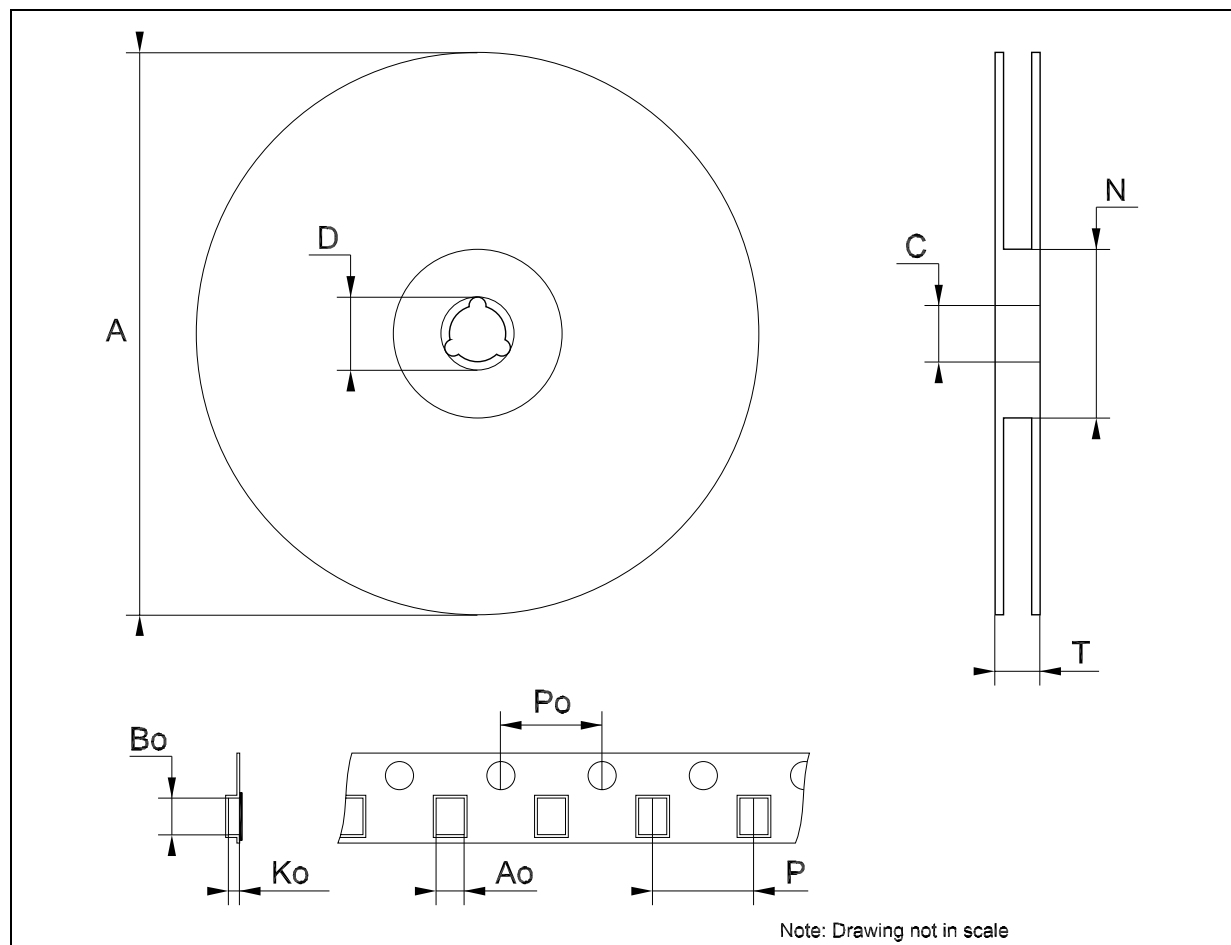
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



0080337D

Tape & Reel SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.4		6.6	0.252		0.260
Bo	9		9.2	0.354		0.362
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



Tape & Reel TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Bo	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319

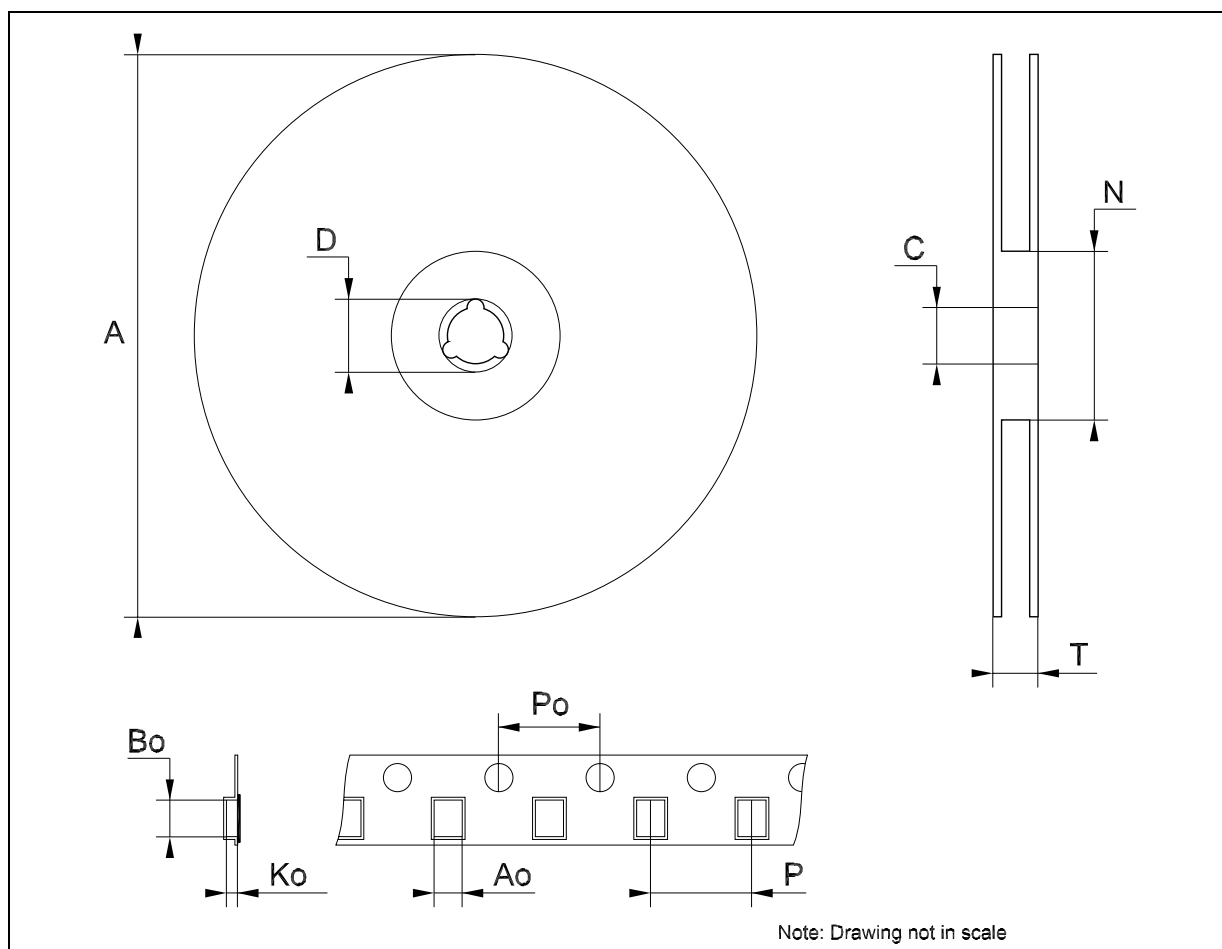


Table 10: Revision History

Date	Revision	Description of Changes
12-Nov-2004	4	Order Codes Revision - pag. 1.

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